

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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SD1013

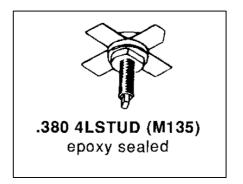
RF & MICROWAVE TRANSISTORS VHF FM MOBILE APPLICATIONS

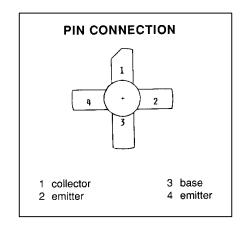
Features

- 150 MHz
- 28 VOLTS
- P_{OUT} = 10 WATTS
- G_P = 10 dB MINIMUM
- COMMON EMITTER CONFIGURATION

DESCRIPTION:

The SD1013 is an epitaxial silicon NPN planar transistor designed primarily for VHF FM applications. The device utilizes emitter ballasting resistors and improved metallization systems to achieve extreme ruggedness under severe operating conditions.





ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
$V_{\sf CBO}$	Collector-Base Voltage	65	V
V _{CEO}	Collector-Emitter Voltage	35	V
V _{CES}	Collector-Base Voltage	65	V
V_{EBO}	Emitter-Base Voltage	4.0	V
Ic	Device Current	1.0	Α
P _{DISS}	Power Dissipation	13	W
T J	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Thermal Data

$R_{TH(J-C)}$	Thermal Resistance Junction-case	13.5	°C/W			



SD1013

ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

STATIC

Symbol	Test Conditions	Value			Unit		
	rest conditions		Min.	Typ.	Max.	Offic	
BV _{CBO}	I _C = 200 mA	$I_E = 0 \text{ mA}$		65			V
BV _{CES}	I _C = 200 mA	$V_{BE} = 0 V$		65			V
BV _{CEO}	I _C = 200 mA	$I_B = 0 \text{ mA}$		35			V
BV_{EBO}	I _E = 10 mA	$I_C = 0 \text{ mA}$		4.0			V
I _{CBO}	V _{CB} = 30 V	$I_E = 0 \text{ mA}$				1.0	mA
HFE	V _{CE} = 5 V	$I_C = 200 \text{ mA}$		5			

DYNAMIC

Symbol	Test Conditions			Value			
Syllibol			Min.	Typ.	Max.	Unit	
P _{OUT}	f = 150 MHz	$P_{IN} = 1.0 W$	$V_{CC} = 28 V$	10			W
G _P	f = 150 MHz	$P_{IN} = 1.0 W$	$V_{CC} = 28 V$	10			dB
Сов	f = 1 MHz	$V_{CB} = 30 \text{ V}$				15	pF

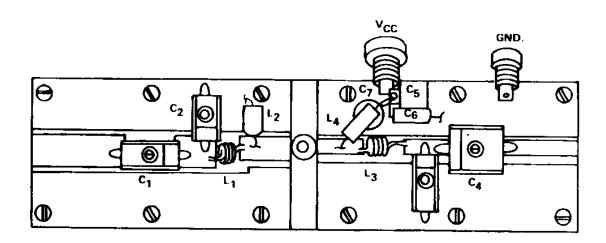
Note: When used at 13.5 Volts, performances are:

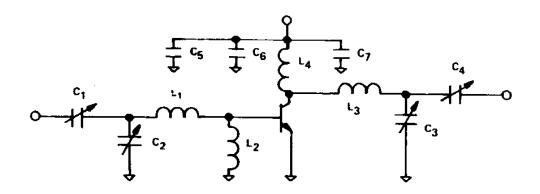
 P_{OUT} = 3.5 Watt typical G_P = 10.5 dB typical



SD1013

TEST CIRCUIT





 C1,C2
 : ARCO 422
 C7
 : .01pF Ceramic Disc

 C3
 : ARCO 421
 L1
 : 3Turns #22, 1/8" I.D.

 C4
 : ARCO 464
 L2
 : RFC Ferroxcube

 C5
 : 1000pF UNELCO
 L3
 : 3 Turns #18, 1/4" I.D

 C6
 : 10μF Electrolytic 35V
 L4
 : .47μh Molded Choke





PACKAGE MECHANICAL DATA

